

(19)



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(11)

**EP 0 543 061 B1**

(12)

## EUROPEAN PATENT SPECIFICATION

(45) Date of publication and mention  
of the grant of the patent:  
15.07.1998 Bulletin 1998/29

(51) Int Cl.<sup>6</sup>: **G02B 5/30, H01S 3/25**

(21) Application number: **91310681.1**

(22) Date of filing: **20.11.1991**

### (54) Light amplifying polarizer

Lichtverstärkungspolarisator

Polariseur amplificateur de lumière

(84) Designated Contracting States:  
**DE GB**

(43) Date of publication of application:  
26.05.1993 Bulletin 1993/21

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(56) References cited:

**EP-A- 361 035**                      **GB-A- 2 220 522**  
**GB-A- 2 231 169**

- **PATENT ABSTRACTS OF JAPAN**, vol. 14, no. 12 (E-871), 11th January 1989; & **JP-A-1 257 386**
- **IEEE PHOTONICS TECHNOLOGY LETTERS**, vol. 2, no. 11, November 1990, pages 794-796, IEEE, New York, US; T. SAITOH et al.: "Low noise characteristics of a GaAs-AlGaAs multiple-quantum-well semiconductor laser amplifier"
- **PATENT ABSTRACTS OF JAPAN**, vol. 10, no. 27 (E-378), 4th February 1986; & **JP-A- 60 187 085**

- **PATENT ABSTRACTS OF JAPAN**, vol. 4, no. 71 (E-012), 24th May 1980; & **JP-A-55 039 612**
- **PATENT ABSTRACTS OF JAPAN**, vol. 13, no. 264 (E-774), 19th June 1989; & **JP-A-1 055 889**
- **IEEE JOURNAL OF QUANTUM ELECTRONICS**, vol. 27, no. 6, June 1991, pages 1830-1836, New York, US; P.-A. BESSE et al.: "Reflectivity minimization of semiconductor laser amplifiers with coated and angled facets considering two-dimensional beam profiles"
- **IEEE TRANSACTIONS ON MICROWAVE THEORY AND TECHNIQUES**, vol. 38, no. 5, May 1990, pages 534-545, New York, US; W.I. WAY et al.: "Applications of traveling-wave laser amplifiers in subcarrier multiplexed lightwave systems"
- **PATENT ABSTRACTS OF JAPAN**, vol. 9, no. 61 (E-303), 19th March 1985; & **JP-A- 59 200 486** (**NIPPON DENSHIN DENWA KOSHA**) 13-11-1984
- **PATENT ABSTRACTS OF JAPAN**, vol. 12, no. 249 (P-730), 14th July 1988; & **JP-A-63 038 903**
- **IEEE PHOTONICS TECHNOLOGY LETTERS** vol. 2, no. 12, December 1990, pages 866-868, IEEE, New York, US; C.R. GILES et al.: "Dynamic gain equalization in two-stage fiber amplifiers"
- **IEEE PHOTONICS TECHNOLOGY LETTERS**, vol. 2, no. 1, January 1990, pages 38-40, IEEE, NEW YORK, US; M.M. CHOY et al.: "A high-gain, high-output saturation power erbium-doped fiber amplifier pumped at 532 nm"
- **ELECTRONICS LETTERS**, vol. 23, no. 24, 19 November 1987, pages 1320-1321, STEVENAGE, HERTS, GB; K. LIU et al.: "10mW superfluorescent single-mode fibre source at 1060nm"
- **PATENT ABSTRACTS OF JAPAN**, vol. 10, no. 358 (P-522), 12th December 1986; & **JP-A-61 156 233** (

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## Description

The present invention relates to a polarizer capable of light amplification.

Conventional polarizers are typically in sheet form or made of calcite (e.g., Glan-Taylor prisms).

The conventional polarizers of these types extract part of the incident light to obtain desired linear polarization, so they inevitably involve the problem of a light loss.

In the case of handling an output of a photodetector which detects linearly polarized light provided from a conventional polarizer, if the noise is mainly a shot noise of the photodetector, the polarizer reduces the light intensity and will deteriorate the S/N ratio of the photodetector's output. Therefore, it is required to take special care in dealing with the light emerging from the polarizer.

The document EP-A-0,361,035 discloses an arrangement of two semiconductor lasers in which one predominantly generates or amplifies waves of a defined other polarisation state and wherein the waves generated or amplified by the two lasers are superimposed on one another.

According to the present invention, a polarizer comprises a semiconductor light amplifier and means for driving the semiconductor light amplifier, wherein the semiconductor light amplifier differentially amplifies a TE mode component and a TM mode component of an input light,

and is characterised in that the semiconductor light amplifier includes an active layer having a thickness of not more than  $0.05\text{ }\mu\text{m}$  so that the TE mode component of an output light has an intensity which is at least a factor of ten times that of the intensity of the TM mode component of the output light.

A polarizer in accordance with this invention permits light to be amplified (i.e., does not cause a light loss), and is capable of producing linearly polarized light that is easy to handle.

Particular embodiments of polarizers in accordance with this invention will now be described with reference to the accompanying drawings; in which:-

Fig. 1 is a diagram showing a polarizer according a first embodiment of the present invention;

Fig. 2 is a sectional view showing a semiconductor light amplifier used in the first embodiment;

Fig. 3 is a block diagram showing the operation of the semiconductor light amplifier;

Fig. 4 is a plan view showing a semiconductor light amplifier of a polarizer according to a second embodiment of the invention;

Fig. 5 is a graph showing a relationship between an amplification factor of a semiconductor light amplifier and a reflectance at its entrance and exit faces;

Fig. 6 is a graph showing a relationship between the reflectance at the entrance and exist faces and their cutting angle with an assumption that an active lay-

er of the semiconductor light amplifier has a refractive index 3.5;

Figs. 7A-7C are plan views showing modifications of the second embodiment shown in Fig. 4;

Fig. 8 is a perspective view showing a semiconductor light amplifier of a polarizer according to a third embodiment of the invention;

Fig. 9 is a sectional view showing an enlarged essential part of a semiconductor light amplifier of a polarizer according to a fourth embodiment of the invention;

Figs. 10A and 10B are sectional views showing how light spreads and is reflected in the essential part shown in Fig. 9;

Fig. 11 is a diagram showing a doped fiber polarizer; Fig. 12 is a diagram showing a modification of the polarizer of Fig. 11;

Figs. 13A and 13B are diagrams showing two examples in which the polarizer of the present invention is combined with the polarizer of Fig. 11 or Fig. 12; and,

Fig. 14 is a block diagram showing an application example in which the polarizer of the invention is incorporated in an E-O voltage detector.

A first embodiment of the present invention is shown in Fig. 1. A polarizer generally indicated by numeral 10 comprises a semiconductor light amplifier 12 and a drive device 14 for driving the semiconductor light amplifier 12. The semiconductor light amplifier 12 has a thinner active layer whose thickness is not more than  $0.05\text{ }\mu\text{m}$ , desirably about  $0.02\text{ }\mu\text{m}$ .

As exemplified in Fig. 2, the semiconductor light amplifier 12 has a SADH (self-aligned double heterojunction) structure, and comprises layers A-I (12A-12I) that are superposed one on another in the direction from an anode 16 towards a cathode 18. In the prior art, layer F, i.e., an active layer 12F, usually has a thickness of about  $0.1\text{ }\mu\text{m}$ . But in the embodiment under consideration, that layer is adjusted to be not thicker than  $0.05\text{ }\mu\text{m}$ , desirably about  $0.02\text{ }\mu\text{m}$ .

Layer A (12A) serves as a Au/Cr contact. Layer B is a p<sup>+</sup>-GaAs layer having Zn diffused in its hatched region. Layers C, E and G (12C, 12E and 12G) have a composition of  $\text{Ga}_{1-x}\text{Al}_x\text{As}$  where  $x = 0.37$ . The active layer 12F has an effective active region (hatched in the figure) whose width and length are about  $3\text{ }\mu\text{m}$  and  $200\text{ }\mu\text{m}$ , respectively. Composition of the active layer 12F is  $\text{Ga}_{1-x}\text{Al}_x\text{As}$  where  $x = 0.028$ .

If, as described above, the active layer 12F is adjusted to have a smaller thickness than in the usual case, the propagation of TM mode light through the active layer 12F is suppressed to lower the factor of light amplification. Thus, the amplification factor of TE mode light is relatively increased to insure that the light emerging from the semiconductor light amplifier 12 is not only linearly polarized but also amplified by a significant degree.

The difference in amplification factor between the TE and TM modes will be described below in detail.

Suppose here that, as shown in Fig. 3, output light from a master laser 20 is input to a semiconductor light amplifier 22 having an end face reflectance R and a cavity length L. As a result of multiple reflections within a Fabry-Perot cavity having an optical gain, the amplification factor G (= Pout/Pin where Pin and Pout are an input signal power to and an output signal power from the semiconductor light amplifier 22, respectively) is given by:

$$G(\phi) = \{(1-R)^2 G_s\} / \{(1-RG_s)^2 + 4G_s R \sin^2(\phi/2)\} \quad (1)$$

where Gs and  $\phi$  are a one-way gain and a go-and-return phase shift in the cavity, respectively. Reference numeral 24 in Fig. 3 represents an isolator.

The one-way gain Gs is expressed as:

$$G_s = \exp(\Gamma g - \alpha_i) L \quad (2)$$

where  $\Gamma$  is a light confinement function, g is an optical gain of the active layer, and  $\alpha_i$  is an absorption coefficient.

Parameter Gs provides an amplification factor for the case of a traveling wave amplifier where the reflectance at both end faces of the cavity is neglected.

With the thinner active layer 12F, the degree of optical confinement of TM mode light,  $\Gamma_{TM}$ , can be reduced and, hence, Gs of TM mode light can be reduced. As a result, the amplification factor G of TM mode light is reduced, and a relationship  $G_E/G_M > 10$  is established where  $G_E$  and  $G_M$  are amplification factors of TM mode light and TE mode light, respectively.

Preferably, a light entrance face 13A and a light exit face 13B of the semiconductor light amplifier 12 are coated with an anti-reflection film 15.

A second embodiment will be described below with reference to Figs. 4 through 7A-7C.

As shown in Fig. 4, which is a top view (see Fig. 1), a polarizer generally indicated by numeral 28 comprises a semiconductor light amplifier 26 whose light entrance and exit faces 26A, 26B are made cutting faces tilted by an angle  $\theta$  where  $10^\circ \leq \theta \leq 16^\circ$ . Shown by reference symbol 26F in Fig. 4 is an active layer.

By tilting the light entrance and exit faces 26A, 26B, only TE mode light is efficiently amplified and selected.

The reason for this favorable phenomenon is explained as follows. First, the go-and-return phase shift  $\phi$  in equation (1) is given by:

$$\begin{aligned} \phi &= 4\pi(v_{in} - v_0)Ln_g/c \\ &= 4\pi Ln_g(1/\lambda_{in} - 1/\lambda_0) \end{aligned} \quad (3)$$

where  $v_{in}$  is a frequency of input signal light (its wavelength is  $\lambda_{in}$ ),  $v_0$  is a resonance frequency (resonance wavelength is  $\lambda_0$ ),  $n_g$  is an effective refractive index in the cavity mode, and c is the velocity of light.

For the sake of simplification, let assume that  $v_{in} = v_0$ . Then,  $\phi$  becomes equal to zero and equation (1) is rewritten as:

$$\begin{aligned} G &= P_{out}/P_{in} \\ &= (1-R)^2 G_s / (1-RG_s)^2. \end{aligned} \quad (1')$$

With the semiconductor light amplifier 12 shown in Fig. 1, a value of 200 has been obtained for G when  $R = 1\%$ . Substituting these values into equation (1') and considering the condition  $G > G_s$ , one can see that Gs is 50.

If  $G_s = 50$  is substituted into equation (1'), the relationship between R and G is obtained as shown in Fig. 5. Since the saturation of the gain g is not considered in Fig. 5, the values of G appears greater than they would actually be. But it can still be seen that a satisfactory reflectance is achieved in the range of R of 0.01-0.03.

On the other hand, the reflectance for light that has reached the end face of the semiconductor light amplifier 26 ( $n_1 = 3.5$ ) after passage through its active layer 26F is dependent on the angle  $\theta$  of the entrance and exit faces 26A and 26B, and there exists a value of  $\theta$  at which the reflectance differs greatly between TM mode light and TE mode light. As is clear from Fig. 6, if  $\theta$  is selected to be  $15^\circ$ , a reflectance for TE mode light is about 0.02 whereas that for TM mode light is 0.6.

Thus, according to Fig. 5, the amplification factor G of TM mode light is negligibly smaller than that of TE mode light and, therefore, only TE mode light can be amplified in an efficient manner.

Equations (1) and (1') stand only where the light reflected by the end faces returns to the active layer. But if the entrance and exit faces of the semiconductor light amplifier are tilted, the proportion that the reflected light from the end face is recoupled to the active layer will become smaller than where the end faces are not tilted, resulting in some deviations from the equations. If the angle  $\theta$  is selected to be  $16^\circ$  in consideration of the reflection characteristics shown in Fig. 6, there will be no loss of TE mode light, which will therefore emerge from the amplifier with no attenuation. On the other hand, about 70% of TM mode light is reflected and some part thereof leaks out from the active layer 26F to cause a loss. As a consequence, only TE mode light will emerge after effective selection.

When  $\theta$  is  $16^\circ$ , Snell's law gives an incident angle  $\psi = 75^\circ$  ( $1 \cdot \sin \psi = 3.5 \cdot \sin 16^\circ$ ). This indicates that light needs to be incident on the entrance face 26A of the semiconductor light amplifier 26 at an incident angle  $\psi$  of  $75^\circ$ . In the above equation of Snell's law, 3.5 repre-

sents a refractive index of the active layer 26F.

In the embodiment under consideration, an anti-reflection film may be provided on the entrance and exit faces 26A, 26B. In this case, the cutting angle  $\theta$  is determined at a value that matches the refractive index of the anti-reflection film so that only TE mode light will selectively be amplified.

In the second embodiment discussed above, the semiconductor light amplifier 26 has a parallelepiped shape as seen from the top. However, this is not the sole case for the geometry of the amplifier, but it may be configured like a semiconductor light amplifier 27A shown in Fig. 7A, in which, as shown from the top, halves of a rectangle are connected together by a parallelepiped active layer 29A. Alternatively, the amplifier may be configured like a semiconductor light amplifier 27B shown in Fig. 7B, in which two rectangles of different sizes are connected together by a trapezoidal active layer 29B. As a further alternative, it may be configured like a semiconductor light amplifier 27C shown in Fig. 7C, which is generally trapezoidal as seen from the top. Shown by reference symbol 29C in Fig. 7C is an active layer.

A third embodiment of the present invention will be described below with reference to Fig. 8.

A semiconductor light amplifier generally indicated by numeral 30 in Fig. 8 has a light waveguide portion 32 which is provided with a metal film 31. Shown by numeral 33 in Fig. 8 is a light amplifying portion of the semiconductor light amplifier 30. The metal film 31 is provided adjacent to the top of an active layer 32A of the light waveguide portion 32.

When light is incident on the semiconductor light amplifier 30, TM mode light, which has an electric field component normal to the metal film 31, is attenuated, so that only TE mode light is selectively amplified. Thus, almost all of the light emerging from the semiconductor light amplifier 30 is the amplified TE mode light and, as a result, desired linearly polarized light can be obtained with amplification.

As in the previous embodiments, an anti-reflection film may be coated on both the light entrance and exit faces of the semiconductor light amplifier 30.

A fourth embodiment of the invention will be described below with reference to Fig. 9.

In this embodiment, a transparent window structure 42 is formed on the end face of an active layer 38F of a semiconductor light amplifier 38 (shown only partially).

In the fourth embodiment, the difference in beam divergence between TM mode light and TE mode light that travel through the window region in the free space mode is effectively used to insure that the TM mode light returning to the active region will be coupled with a different efficiency than the TE mode light.

Stated more specifically, the TM mode light spreads at a wider angle to enter the window region as shown in Fig. 10A (vertical sectional view), so that a smaller amount of light will be reflected by the cleaved surface 40 to return to the active layer 38F, whereby the coupling

efficiency is low. On the other hand, as shown in Fig. 10B (horizontal sectional view), the TE mode light spreads at a narrower angle to enter the window region, so that, compared to the TM mode light, more of the light will return to the active layer 38F, resulting in a relatively high coupling efficiency.

If the effective reflectance  $R$  is 0.002 and 0.005 for the TE and TM modes, respectively, one can readily see from Fig. 5 that only TE mode light will be amplified with high efficiency.

Although the first to fourth embodiments are described as amplifying TE mode light, it should be noted that structures of the embodiments may be modified to provide amplification of TM mode light, specifically in the case of the fourth embodiment.

In Fig. 11, a polarizer generally indicated by numeral 47 is constructed such that a polarization maintaining optical fiber 46 doped with a rare earth element, which serves as a fiber amplifier, is used to pick up desired linearly polarized light with amplification. Exemplary rare earth elements that can be used as a dopant include Nd, Er, Ho, Sm and Tm, and their ions.

Shown by numeral 48 in Fig. 11 is an excitation light source. Excitation light emitted from the light source 48 is combined with the input light by a half mirror 50, and the combined light is input to the rare-earth-element doped, polarization maintaining optical fiber 47 from its entrance face.

In Fig. 11, the half mirror 50 is used to combine the input light and the excitation light. A modification is shown in Fig. 12, in which a polarizer 49 is constructed such that both the input light and the excitation light are guided by respective optical fibers 52 and combined by an optical coupler 54, with the combined light being then input to a rare-earth-element doped, polarization maintaining optical fiber 46.

The output light from the rare-earth-element doped, polarization maintaining optical fiber 46 usually contains an excitation light component as noise. If a large amount of the excitation light component is likely to be contained, a filter, dichroic mirror, prism or some other element may be provided after the exit face of the optical fiber 46.

In the case of using the rare-earth-element doped, polarization maintaining optical fiber 46, an anti-reflection film may be coated on both the entrance and exit faces, or those faces may be made cutting faces having an appropriate tilt angle such as a Brewster angle, or may be provided with a window structure. In these modifications, the purity of the output linearly polarized light can further be increased.

The latter two cases will be described in more detail. If the sectional shape of the core of the rare-earth-element doped, polarization maintaining optical fiber 46 is elliptical or rectangular, the end face is tilted such that the major axis or longitudinal axis of the core coincides with the major axis of a resulting tilted end face. If the tilt angle is equal to a Brewster angle, a light component

having a polarization direction along the major axis of the core is solely input and output with a small loss. As a result, there can be caused a difference in the amplification factors of such a light component and a light component having a polarization direction perpendicular thereto. The provision of the window structure on the end faces will cause the same effects as shown in Figs. 9, 10A and 10B.

In the polarizers of Figs. 11 and 12, only one unit of polarizer is used. However, various modifications may be made to obtain output light that has been linearly polarized to an even greater extent.

For example, two polarizers 60A and 60B comprising a semiconductor light amplifier of the present invention are cascade-connected via an optical fiber 62 as shown in Fig. 13A. Alternatively, a polarizer 60 comprising a semiconductor light amplifier is combined with a polarizer 64 comprising a rare-earth-element doped, polarization maintaining optical fiber 64A as shown in Fig. 13B. Shown by symbols 64B and 64C in Fig. 13B are an excitation light source and an optical coupler, respectively. In the case of using a polarization maintaining optical fiber, more purely polarized light can be obtained simply by changing its length rather than by connecting a plurality of units in series.

A practical application of the polarizer of the invention is shown in Fig. 14, in which it is incorporated in an electrooptic (E-O) voltage detector that uses an E-O device. The system shown in Fig. 14 comprises a conventional polarizer 56; an E-O modulator 58 to which probing light transmitted through the polarizer 56 is supplied, and which is modulated by an electric signal to be measured; a light amplifying polarizer 60 of the invention which amplifies an output light of the E-O modulator 58; and a photodetector 62 that converts an output light of the light amplifying polarizer 60 to an electric signal.

In the case of a conventional system corresponding to the above one, polarizers would suffer from a large light loss. But in the system of Fig. 14, the output light of the E-O modulator 58 is sufficiently amplified by the light amplifying polarizer 60, which improves the S/N ratio of the output signal from the photodetector 62, and facilitates the handling of the light at the stages after the light amplifying polarizer 60.

#### Claims

1. A polarizer comprising a semiconductor light amplifier and means for driving the semiconductor light amplifier, wherein the semiconductor light differentially amplifies a TE mode component and a TM mode component of an input light, characterised in that the semiconductor light amplifier (12,26,27,33) includes an active layer (12F,26F,38F) having a thickness of not more than  $0.05\ \mu\text{m}$  so that the TE mode component of an output light has an intensity which is at least a factor of ten times that of the in-

tensity of the TM mode component of the output light.

2. A polarizer according to claim 1, wherein at least one of entrance and exit faces (26A,26B) of the semiconductor light amplifier (12,26,27,33) is tilted by 10 to 16 degrees relative to a longitudinal axis of the polarizer.
3. A polarizer according to claim 1 or 2, wherein the semiconductor light amplifier (33) comprises a light waveguide portion (32) which includes an active layer and a metal film (31) provided adjacent the active layer.
4. A polarizer according to any one of the preceding claims, wherein entrance and exit faces of the semiconductor light amplifier (12,26,27,33) are provided with an anti-reflection film.
5. A polarizer according to any one of the preceding claims, wherein the semiconductor light amplifier (12,26,27,33) includes a transparent window structure on at least one of its entrance and exit faces.
6. A polarizer system comprising a polarizer according to any one of the preceding claims, in combination with a series connected polarizer comprising:
  - a polarization maintaining optical fiber (46) doped with a rare earth element;
  - a light source (48,64B) for emitting excitation light for the polarization maintaining optical fiber (46); and,
  - means (50,54) for combining input light and the excitation light to form combined light to be input to the polarization maintaining optical fiber (46).
7. A polarizer system according to claim 6, in which in the series connected polarizer, at least one of an entrance and an exit face of the polarization maintaining optical fiber (46) is tilted.
8. A polarizer system according to claim 7, in which the combining means is a half mirror (50) or an optical coupler (54).

#### Patentansprüche

1. Polarisator mit einem Halbleiter-Lichtverstärker und einer Einrichtung zum Ansteuern des Halbleiter-Lichtverstärkers, wobei das Halbleiterlicht eine TE-Modus-Komponente und eine TM-Modus-Komponente eines Eingangslichts differential verstärkt, dadurch gekennzeichnet, daß der Halbleiter-Lichtverstärker (12, 26, 27, 33) eine aktive Schicht (12F,

26F, 38F) mit einer Dicke von höchstens 0,05 µm umfaßt, so daß die TE-Modus-Komponente eines Ausgangslichts eine Intensität hat, die mindestens das Zehnfache der Intensität der TM-Modus-Komponente des Ausgangslichts beträgt.

2. Polarisator nach Anspruch 1, wobei eine der beiden Flächen - der Eintritts- und der Austrittsfläche (26A, 26B) - des Halbleiter-Lichtverstärkers (12, 26, 27, 33) um 10 bis 16 Grad zur Längsachse des Polarisators geneigt ist.

3. Polarisator nach einem der Ansprüche 1 oder 2, wobei der Halbleiter-Lichtverstärker (33) einen Lichtwellenleiter (32) umfaßt, der eine aktive Schicht und einen Metallfilm (31) neben der aktiven Schicht aufweist.

4. Polarisator nach einem der vorangehenden Ansprüche, wobei die Eintritts- und die Austrittsfläche des Halbleiter-Lichtverstärkers (12, 26, 27, 33) einen Antireflexionsfilm aufweisen.

5. Polarisator nach einem der vorangehenden Ansprüche, wobei der Halbleiter-Lichtverstärker (12, 26, 27, 33) eine transparente Fenstervorrichtung auf mindestens einer der beiden Flächen - der Eintritts- und der Austrittsfläche - aufweist.

6. Polarisatorsystem, welches einen Polarisator nach einem der vorangehenden Ansprüche in Kombination mit einem vorgeschalteten Polarisator umfaßt, mit:

einem die Polarisation aufrechterhaltenden und mit einem seltenen Erdmetall dotierten Lichtleiter (46), einer Lichtquelle (48, 64B) zum Emittieren von Erregerlicht für den die Polarisation aufrechterhaltenden Lichtleiter (46) und einer Einrichtung (50, 54) zum Kombinieren des Eingangslichts und des Ausgangslichts zwecks Ausbildung von zusammengesetztem Licht, welches in den die Polarisation aufrechterhaltenden Lichtleiter (46) eingegeben wird.

7. Polarisatorsystem nach Anspruch 6, wobei im vorgeschalteten Polarisator mindestens eine der beiden Flächen - Eintritts- und Austrittsfläche - des die Polarisation aufrechterhaltenden Lichtleiters (46) geneigt ist.

8. Polarisatorsystem nach Anspruch 7, wobei die Kombinationseinrichtung ein Halbspiegel (50) oder eine optische Kopplungsvorrichtung (54) ist.

## Revendications

1. Polariseur comportant un amplificateur de lumière à semi-conducteur et un moyen pour commander l'amplificateur de lumière à semi-conducteur, dans lequel l'amplificateur de lumière à semi-conducteur amplifie de manière différentielle une composante en mode TE et une composante en mode TM d'une lumière d'entrée, caractérisé en ce que l'amplificateur de lumière à semi-conducteur (12, 26, 27, 33) comporte une couche active (12F, 26F, 38F) dont l'épaisseur n'est pas supérieure à 0,05 µm, de telle sorte que la composante en mode TE d'une lumière de sortie présente une intensité qui est au moins le décuple de l'intensité de la composante en mode TM de la lumière de sortie.

2. Polariseur selon la revendication 1, dans lequel au moins l'une parmi les faces d'entrée et de sortie (26A, 26B) de l'amplificateur de lumière à semi-conducteur (12, 26, 27, 33) est inclinée de 10 à 16 degrés par rapport à un axe longitudinal du polariseur.

3. Polariseur selon les revendications 1 ou 2, dans lequel l'amplificateur de lumière à semi-conducteur (33) comporte une partie (32) de guide d'ondes lumineuses qui comporte une couche active et un film métallique (31) adjacent à la couche active.

4. Polariseur selon l'une quelconque des revendications précédentes, dans lequel les faces d'entrée et de sortie de l'amplificateur de lumière à semi-conducteur (12, 26, 27, 33) sont dotées d'un film anti-reflets.

5. Polariseur selon l'une quelconque des revendications précédentes, dans lequel l'amplificateur de lumière à semi-conducteur (12, 26, 27, 33) comporte une structure à fenêtre transparente sur au moins l'une de ses faces d'entrée et de sortie.

6. Système de polariseur comportant un polariseur selon l'une quelconque des revendications précédentes, en combinaison avec un polariseur raccordé en série, comportant:

- une fibre optique (46) de maintien de la polarisation, dopée avec un élément des terres rares;
- une source de lumière (48, 64B) pour émettre une lumière d'excitation pour la fibre optique (46) de maintien de la polarisation; et
- un moyen (50, 54) pour combiner une lumière d'entrée et la lumière d'excitation pour former une lumière combinée à introduire dans la fibre optique (46) de maintien de la polarisation.

7. Système de polariseur selon la revendication 6, dans lequel, dans le polariseur raccordé en série,

au moins l'une parmi une face d'entrée et une face de sortie de la fibre optique (46) de maintien de la polarisation est inclinée.

8. Système de polariseur selon la revendication 7, dans lequel le moyen de combinaison est un demi-miroir (50) ou un coupleur optique (54).

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FIG. 1

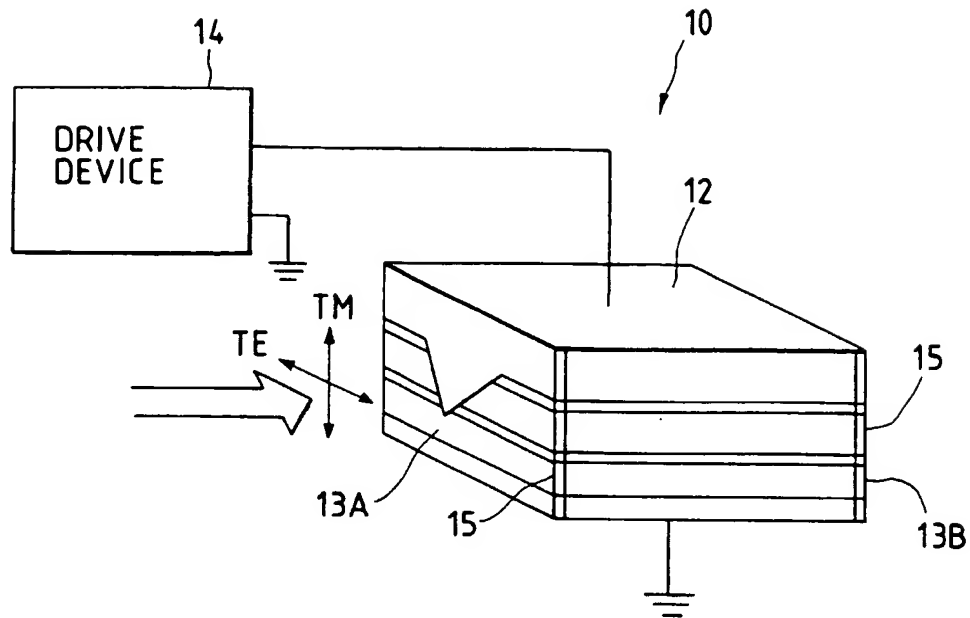


FIG. 2

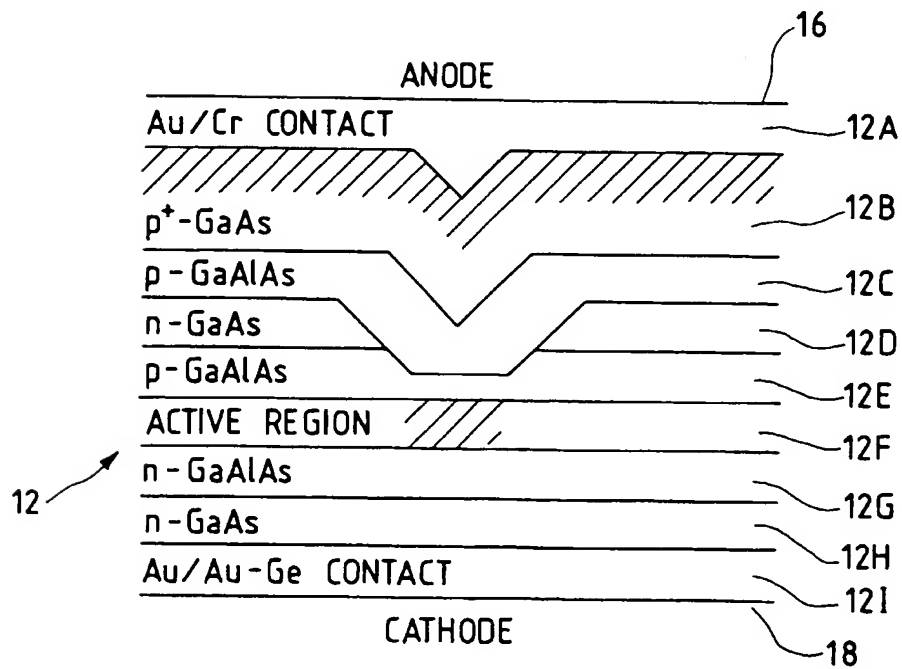




FIG. 3

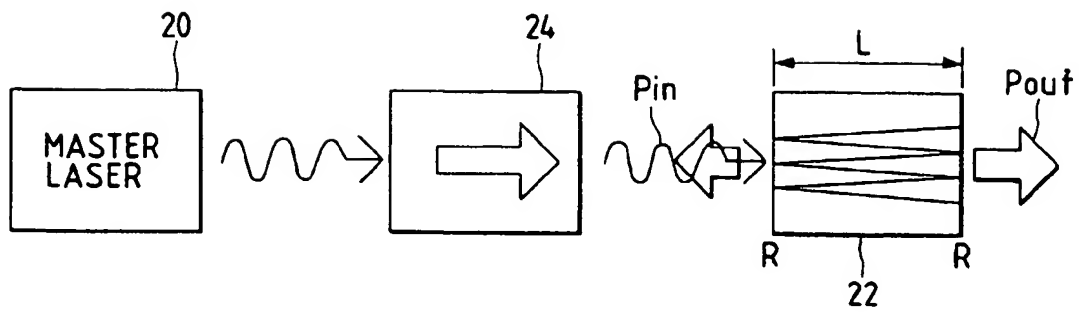


FIG. 4

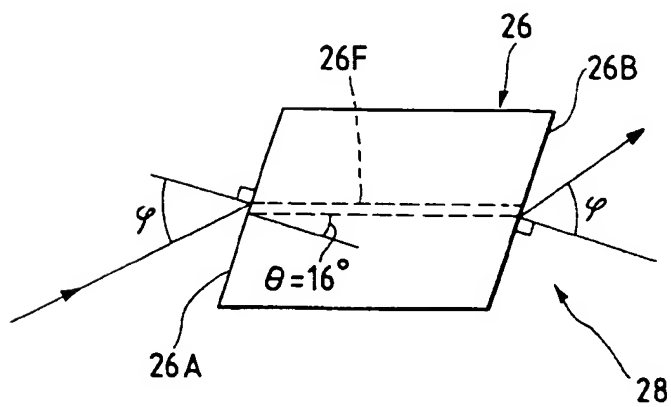


FIG. 5

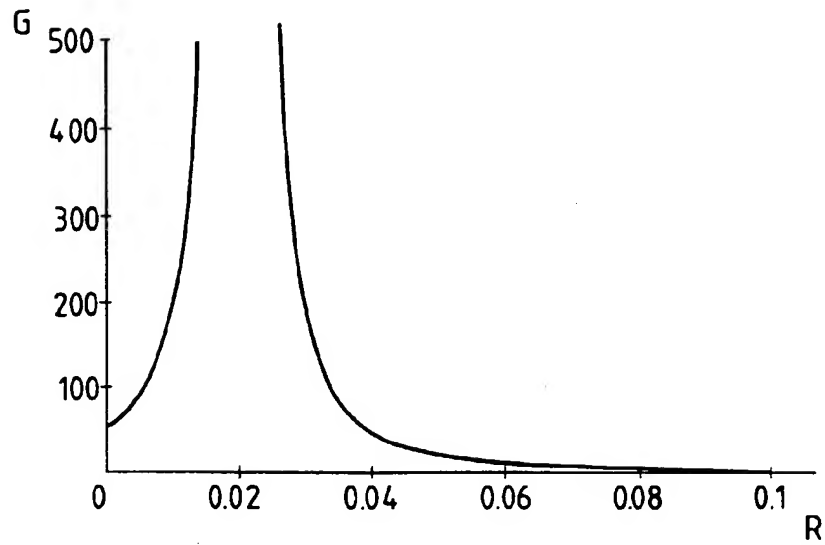


FIG. 6

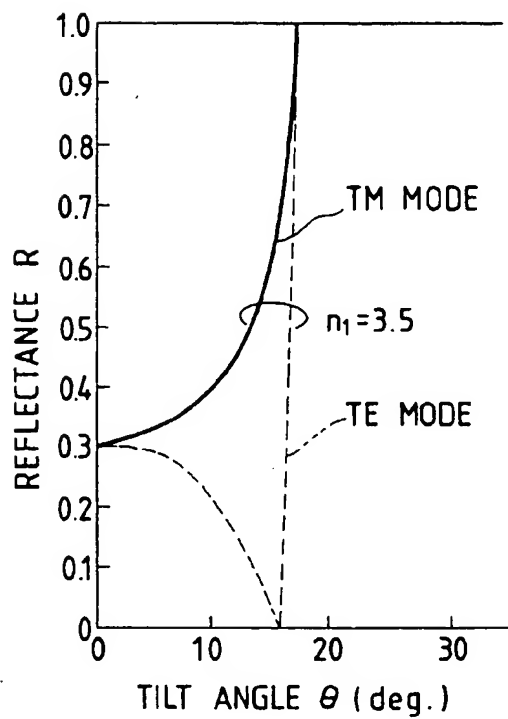


FIG. 7A

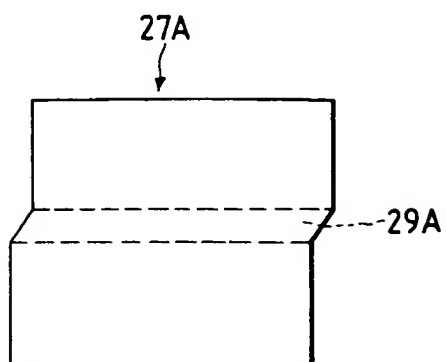


FIG. 7B

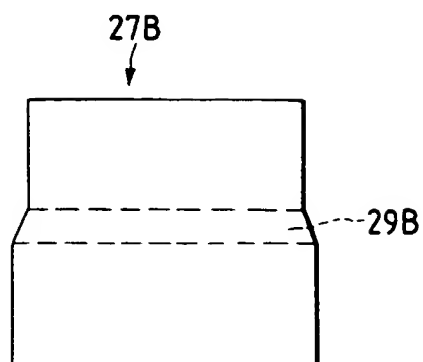


FIG. 7C

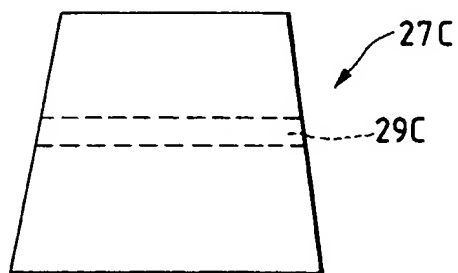


FIG. 8

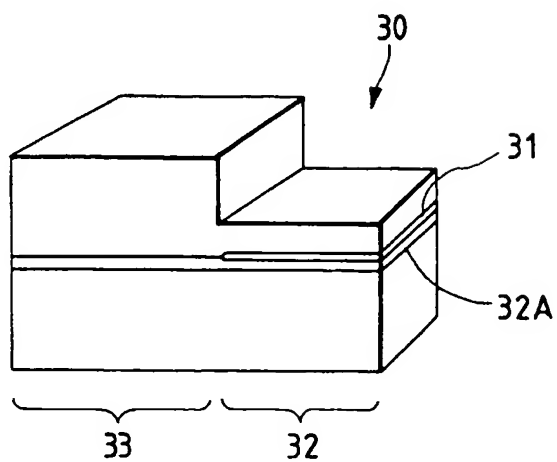


FIG. 9

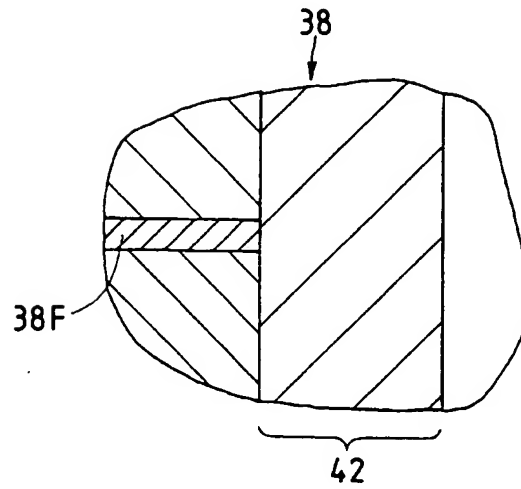


FIG. 10A

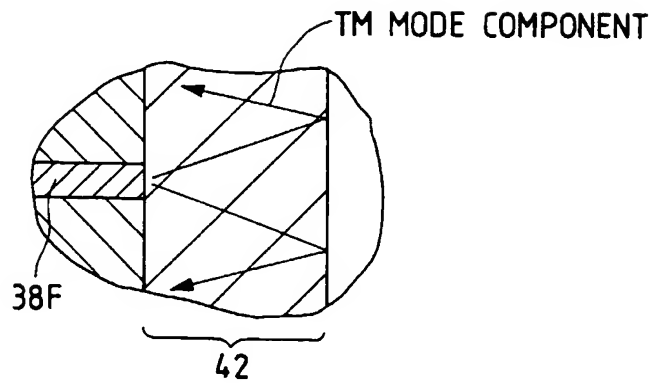


FIG. 10B

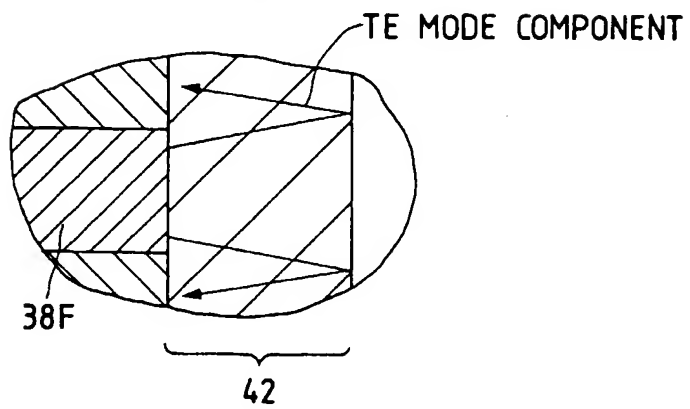


FIG. 11

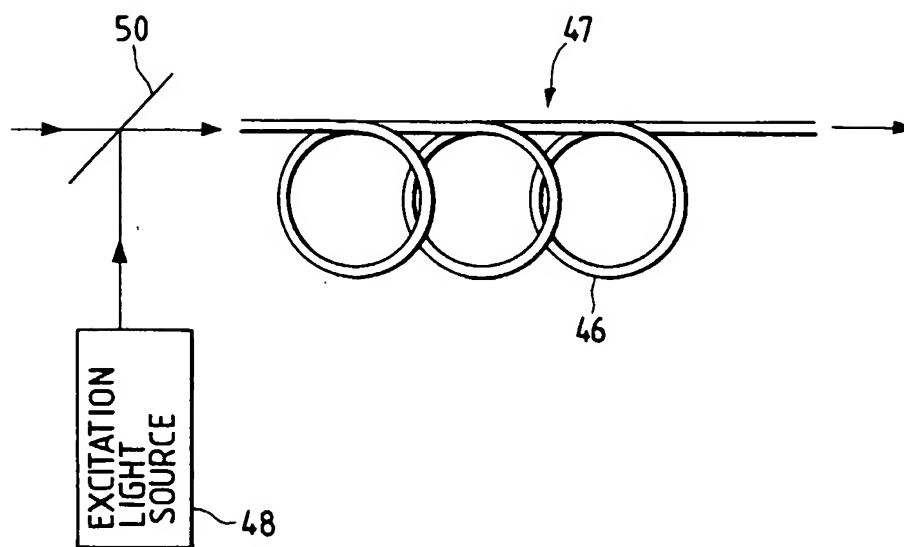


FIG. 12

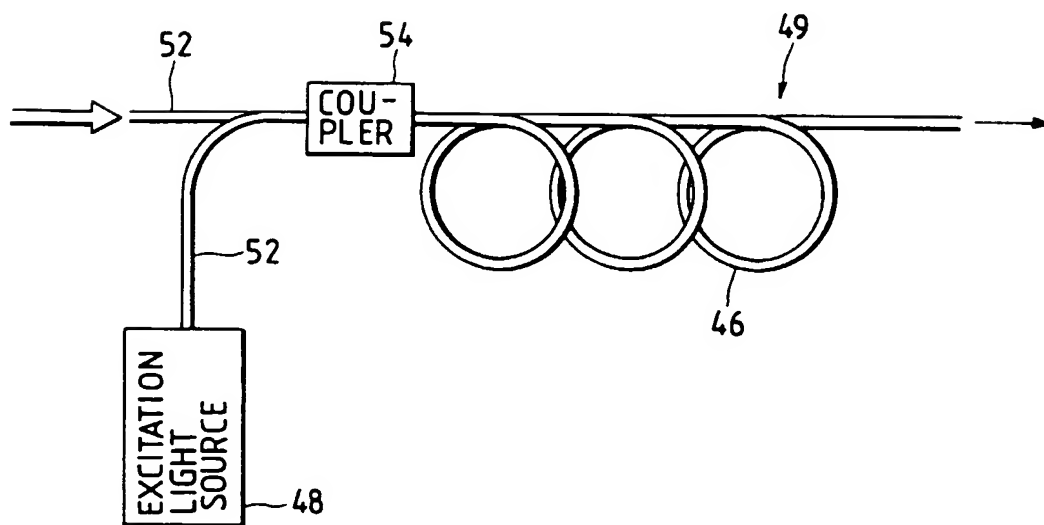


FIG. 13A

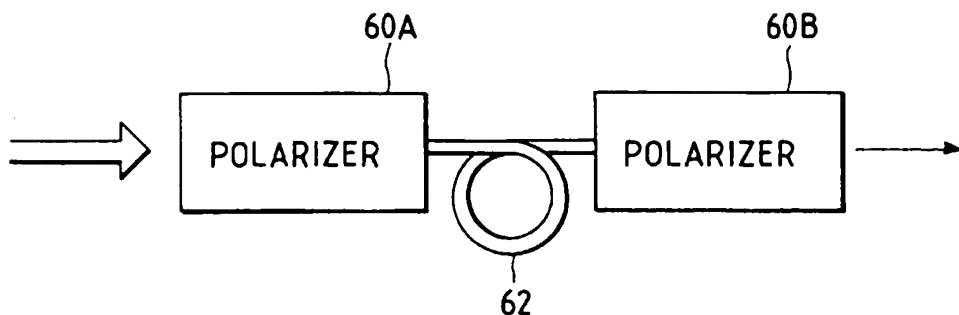


FIG. 13B

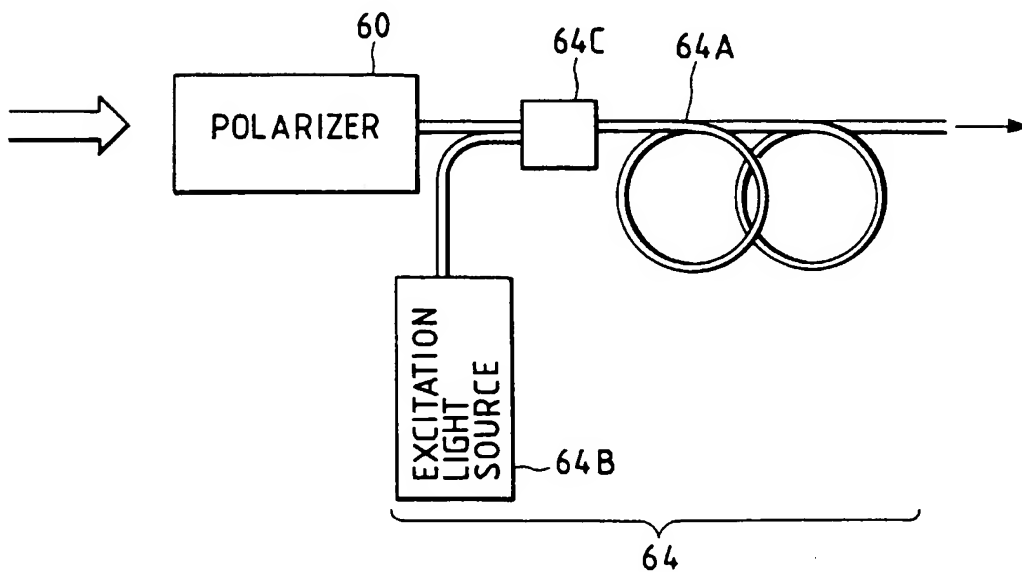


FIG. 14

